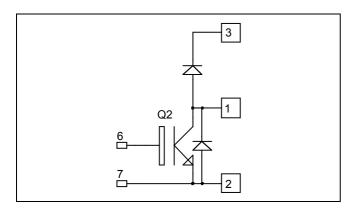
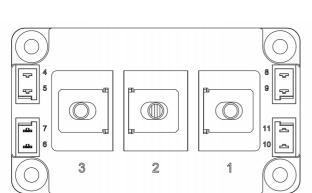


Boost chopper Trench + Field Stop IGBT4 Power Module

$$V_{CES} = 1200V$$

 $I_{C} = 700A$ @ $T_{C} = 80^{\circ}C$





Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Trench + Field Stop IGBT 4 Technology
 - Low voltage drop
 - Low leakage current
 - Low switching losses
 - Soft recovery parallel diodes
 - Low diode VF
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- High level of integration
- M6 power connectors

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
I_{C}	Continuous Collector Current	$T_C = 25^{\circ}C$	840	
	Continuous Collector Current $T_C=$		700	Α
I_{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	1800	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_C = 25^{\circ}C$	3000	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	1200A @ 1100V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V$, $V_{CE} =$			5	mA	
V	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.8	2.2	V
$V_{CE(sat)}$	Conector Emitter saturation voltage	$I_{\rm C} = 600 A$	$T_j = 125$ °C		2.2		v
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 11mA$		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				800	nA

Dynamic Characteristics

	Characteristic	Test Conditions	r	Min	Typ	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$	$V_{GF} = 0V$				
Coes	Output Capacitance	$V_{CE} = 25V$			2.3		nF
C_{res}	Reverse Transfer Capacitance	f = 1MHz	f = 1MHz				
Q_{G}	Gate charge	V_{GE} = -8V / 15V I_{C} =600A	V_{GE} = -8V / 15V ; V_{CE} =600V I_{C} =600A				μС
$T_{d(on)}$	Turn-on Delay Time		Inductive Switching (25°C)				
T_{r}	Rise Time	$V_{GE} = \pm 15V$			40		
$T_{d(off)}$	Turn-off Delay Time	$V_{CE} = 600V$ $I_{C} = 600A$			380		ns
$T_{\rm f}$	Fall Time	$R_G = 0.8\Omega$	_				
$T_{d(on)}$	Turn-on Delay Time		Inductive Switching (150°C) $V_{GE} = \pm 15V$				ns
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$ $V_{CE} = 600V$					
$T_{d(off)}$	Turn-off Delay Time	$I_{\rm C} = 600 \text{V}$			450		ns
T_{f}	Fall Time	$R_G = 0.8\Omega$			80		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{CE} = 600V$	$T_{J} = 150^{\circ}C$		54		mJ
E _{off}	Turn-off Switching Energy	$I_C = 600A$ $R_G = 0.8\Omega$	$T_{J} = 150^{\circ}C$		58		mJ
I_{sc}	Short Circuit data		$V_{GE} \le 15V$; $V_{Bus} = 900V$ $t_p \le 10\mu s$; $T_j = 150^{\circ}C$		2400		A

Chopper ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
V_{RRM}	Maximum Repetitive Reverse Voltage			1200			V
I_{RRM}	Maximum Reverse Leakage Current	V _R =1200V	$T_j = 25^{\circ}C$ $T_i = 150^{\circ}C$			250 2000	μА
I_{F}	DC Forward Current		$T_{\rm C} = 80^{\circ} \rm C$		600	2000	A
V	Die de Fermand Waltern	$I_F = 600A$	$T_i = 25^{\circ}C$		1.7	2.2	17
V_{F}	Diode Forward Voltage	$V_{GE} = 0V$	$T_{\rm j} = 150^{\circ}{\rm C}$		1.65		V
+	Reverse Recovery Time	1 - 6004	$T_j = 25$ °C		155		ns
t _{rr}			$T_{\rm j} = 150^{\circ}{\rm C}$		300		115
0	Reverse Recovery Charge	$ \begin{cases} I_F = 600A \\ V_R = 600V \end{cases} $	$T_j = 25^{\circ}C$		53		μС
Q_{rr}	Reverse Recovery Charge	$di/dt = 7000A/\mu s$	$T_j = 150$ °C		110		μС
E_{rr}	Reverse Recovery Energy]	$T_j = 25$ °C		23		mJ
Ŀ _{rr}	Reverse Recovery Energy		$T_j = 150$ °C		46		IIIJ



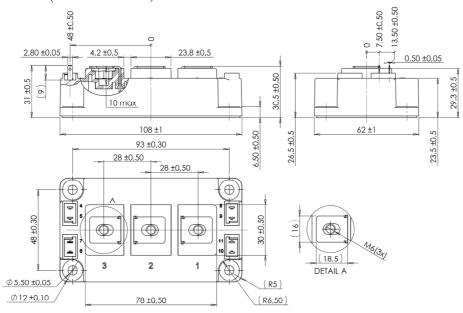
IGBT Parallel protection diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
V_{RRM}	Maximum Repetitive Reverse Voltage			1200			V
I_{RRM}	Maximum Reverse Leakage Current	V _R =1200V	$T_j = 25^{\circ}C$			100	μA
I_{F}	DC Forward Current		$T_{\rm j} = 150^{\circ} \text{C}$ $T_{\rm C} = 80^{\circ} \text{C}$		75	500	A
V	Die de Ferryand Weltere	$I_F = 75A$	$T_j = 25^{\circ}C$		1.7	2.2	V
$V_{\rm F}$	Diode Forward Voltage	$I_F = 75A$ $V_{GE} = 0V$	$T_{\rm j} = 150^{\circ}{\rm C}$		1.65		\ \ \
t	Reverse Recovery Time	Т	$T_j = 25^{\circ}C$		155		ns
t _{rr}			$T_{\rm j} = 150^{\circ}{\rm C}$		300		115
0	VIII TECTORS RECOVERY CHARGE	$ \mathbf{x}_{\mathbf{x}} \mathbf{x}_{\mathbf{x}} \mathbf{x}_{\mathbf{x}} $		7.3		μС	
Qrr			$T_{j} = 150^{\circ}C$		15.2		μС
E_{rr}	Reverse Recovery Energy		$T_j = 25^{\circ}C$		2.6		mJ
Lin			$T_{i} = 150^{\circ}C$		5.5		1113

Thermal and package characteristics

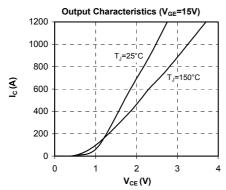
Symbol	Characteristic					Тур	Max	Unit
	Junction to Case Thermal Resistance IGBT Chopper diode				0.05			
R_{thJC}			per diode			0.10	°C/W	
		IGBT parallel diode					0.62	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz							V
T_{J}	Operating junction temperature range						175	
T_{STG}	Storage Temperature Range				-40		125	°C
$T_{\rm C}$	Operating Case Temperature						125	
Torque	Mounting torque	For term	inals	M6	3		5	N.m
Torque	Mounting torque To Heatsi		sink	M6	3		5	18.111
Wt	Package Weight						350	g

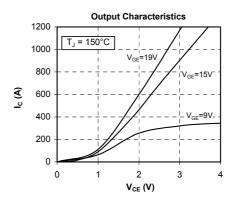
D3 Package outline (dimensions in mm)

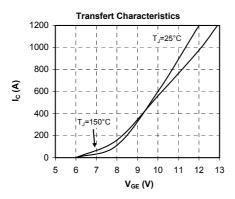


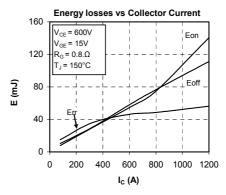


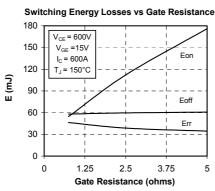
Typical Performance Curve

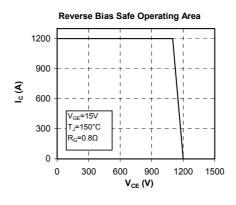


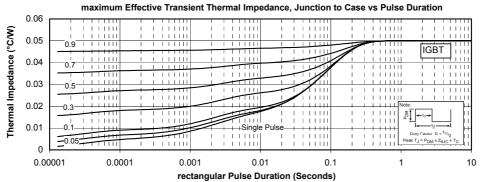








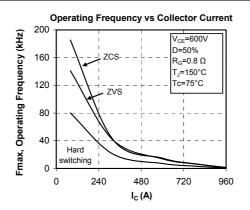


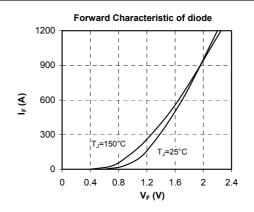


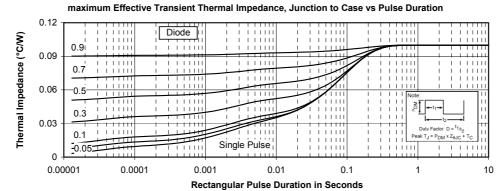
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